

**Amendment to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Previously Presented) A radio frequency amplifier module, comprising:  
a module substrate;  
a radio frequency power amplifier part which is arranged on said module substrate and amplifies a power of a radio frequency signal;  
a bias control part which is arranged on said module substrate and controls operation of said radio frequency power amplifier part with a bias voltage; and  
a bias supply line for supplying the bias voltage from said bias control part to said radio frequency power amplifier part, said bias supply line being connected between said radio frequency power amplifier part and said bias control part,  
wherein said bias supply line comprises a low pass filter which brings attenuation to a radio frequency signal leaking from said radio frequency power amplifier part to said bias control part.
2. (Original) The radio frequency amplifier module according to claim 1,  
wherein said radio frequency power amplifier part is constituted as a semiconductor integrated circuit formed on a semiconductor substrate and said bias supply line is formed on said semiconductor substrate.

3. (Original) The radio frequency amplifier module according to claim 1,  
wherein said bias control part is constituted as a semiconductor integrated circuit formed on a semiconductor substrate and said bias supply line is formed on said semiconductor substrate.

4. (Original) The radio frequency amplifier module according to claim 1,  
wherein said radio frequency power amplifier part and said bias control part are constituted as a semiconductor integrated circuit formed on the same semiconductor substrate and said bias supply line is formed on said semiconductor substrate.

5. (Original) The radio frequency amplifier module according to claim 1,  
wherein said bias supply line is formed on said module substrate.

6. (Cancelled)

7. (Previously Presented) The radio frequency amplifier module according to claim 1,

wherein said bias supply line includes at least one bonding pad having a capacitance component to a ground and a bonding wire formed via said at least one bonding pad.

8. (Previously Presented) The radio frequency amplifier module according to claim 7, further comprising:

a second substrate formed on said module substrate,  
wherein one part of a plurality of bonding pads included in said at least one bonding pad is formed on said module substrate and the other part of said plurality of bonding pads is formed on said second substrate.

9. (New) The radio frequency amplifier module according to claim 7,  
wherein said radio frequency power amplifier part is constituted as a semiconductor integrated circuit formed on a semiconductor substrate and said bias supply line is formed on said semiconductor substrate.

10. (New) The radio frequency amplifier module according to claim 7,  
wherein said bias control part is constituted as a semiconductor integrated circuit formed on a semiconductor substrate and said bias supply line is formed on said semiconductor substrate.

11. (New) The radio frequency amplifier module according to claim 7,  
wherein said radio frequency power amplifier part and said bias control part are constituted as a semiconductor integrated circuit formed on the same semiconductor substrate and said bias supply line is formed on said semiconductor substrate.

12. (New) The radio frequency amplifier module according to claim 7,  
wherein said bias supply line is formed on said module substrate.